

March 2003

LMV341/LMV342/LMV344

Single with Shutdown/Dual/Quad General Purpose, 2.7V, Rail-to-Rail Output, 125°C, Operational Amplifiers

General Description

The LMV341/342/344 are single, dual, and quad low voltage, and low power Operational Amplifiers. They are designed specifically for low voltage portable applications. Other important product characteristics are low input bias current, rail-to-rail output, and wide temperature range.

The patented class AB turnaround stage significantly reduces the noise at higher frequencies, power consumption, and offset voltage. The PMOS input stage provides the user with ultra-low input bias current of 20fA (typical) and high input impedance.

The industrial-plus temperature range of -40°C to 125°C allows the LMV341/342/344 to accommodate a broad range of extended environment applications. LMV341 expands National Semiconductor's Silicon Dust™ amplifier portfolio offering enhancements in size, speed, and power savings. The LMV341/342/344 are guaranteed to operate over the voltage range of 2.7V to 5.0V and all have rail-to-rail output.

The LMV341 offers a shutdown pin that can be used to disable the device. Once in shutdown mode, the supply current is reduced to 45pA (typical). The LMV341/342/344 have 29nV Voltage Noise at 10KHz, 1MHz GBW, 1.0V/ μ s Slew Rate, 0.25mVos, and 0.1 μ A shutdown current (LMV341.)

The LMV341 is offered in the tiny SC70-6L package, the LMV342 in space saving MSOP-8 and SOIC-8, and the LMV344 in TSSOP-14 and SOIC-14. These small package amplifiers offer an ideal solution for applications requiring

minimum PC board footprint. Applications with area constrained PC board requirements include portable electronics such as cellular handsets and PDAs.

Features

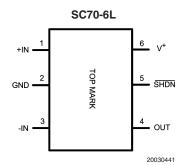
(Typical 2.7V Supply Values; Unless Otherwise Noted)

- Guaranteed 2.7V and 5V specifications
- Input referred voltage noise (@10kHz) 29nV/√Hz
- Supply current (per amplifier) 100µA ■ Gain bandwidth product 1.0MHz
- Slew rate 1.0V/µs
- Shutdown Current (LMV341) 45pA
- Turn-on time from shutdown (LMV341) 5µs
- Input bias current 20fA

Applications

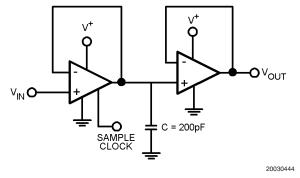
- Cordless/cellular phones
- Laptops
- PDAs
- PCMCIA/Audio
- Portable/battery-powered electronic equipment
- Supply current monitoring
- Battery monitoring
- Buffer
- Filter
- Driver

Connection Diagram



Top View
Order Number
LMV341MG, LMV341MGX
LMV342MM, LMV342MMX
LMV342MA, LMV342MAX
LMV344MT, LMV344MTX
LMV344MA, LMV344MAX

Sample and Hold Circuit



Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

ESD Tolerance (Note 2)

Machine Model 200V Human Body Model 2000V

Differential Input Voltage \pm Supply Voltage Supply Voltage (V $^+$ -V $^-$) 5.5V

Supply Voltage (V + -V -) 5.5V

Output Short Circuit to V + (Note 3)

Output Short Circuit to V - (Note 4)

Storage Temperature Range -65°C to 150°C Junction Temperature (Note 5) 150°C

Mounting Temperature

Infrared or Convection Reflow

(20 sec.) 235°C

Wave Soldering Lead Temp.

(10 sec.) 260°C

Operating Ratings (Note 1)

Temperature Range -40°C to 125°C

Thermal Resistance (θ_{JA})

6-Pin SC70 414°C/W 8-Pin SOIC 190°C/W 8-Pin MSOP 235°C/W 14-Pin TSSOP 155°C/W

14-Pin SOIC 145°C/W

2.7V DC Electrical Characteristics (Note 10)

Unless otherwise specified, all limits guaranteed for $T_J = 25^{\circ}C$, $V^+ = 2.7V$, $V^- = 0V$, $V_{CM} = V^+/2$, $V_O = V^+/2$ and $R_L > 1M\Omega$. **Boldface** limits apply at the temperature extremes.

			Min	Тур	Max	
Symbol	Parameter	Conditions	(Note 7)	(Note 6)	(Note 7)	Units
V_{OS}	Input Offset Voltage	LMV341		0.25	4	
					4.5	mV
		LMV342/LMV344		0.55	5	111 V
					5.5	
TCVos	Input Offset Voltage Average			1.7		μV/°C
	Drift					
I_B	Input Bias Current			0.02	120	pA
					250	
l _{os}	Input Offset Current			6.6		fA
Is	Supply Current	Per Amplifier		100	170	μΑ
					230	
		Shutdown Mode, V _{SD} = 0V		45pA	1µA	
		(LMV341)			1.5µA	
CMRR	Common Mode Rejection	$0V \le V_{CM} \le 1.7V$	56	80		dB
	Ratio	$0V \le V_{CM} \le 1.6V$	50			
PSRR	Power Supply Rejection Ratio	$2.7V \le V^+ \le 5V$	65	82		dB
			60			
V_{CM}	Input Common Mode Voltage	For CMRR ≥ 50dB	0	-0.2 to 1.9	1.7	V
				(Range)		
A _V	Large Signal Voltage Gain	$R_L = 10k\Omega$ to 1.35V	78	113		
			70			dB
		$R_L = 2k\Omega$ to 1.35V	72	103		uБ
			64			
V_{O}	Output Swing	$R_L = 2k\Omega$ to 1.35V		24	60	
					95	
			60	26		
			95			mV
		$R_L = 10k\Omega$ to 1.35V		5.0	30	111 V
					40	
			30	5.3		
			40			

2.7V DC Electrical Characteristics (Note 10) (Continued)

Unless otherwise specified, all limits guaranteed for $T_J = 25^{\circ}C$, $V^+ = 2.7V$, $V^- = 0V$, $V_{CM} = V^+/2$, $V_O = V^+/2$ and $R_L > 1M\Omega$. **Boldface** limits apply at the temperature extremes.

			Min	Тур	Max	
Symbol	Parameter	Conditions	(Note 7)	(Note 6)	(Note 7)	Units
Io	Output Short Circuit Current	Sourcing LMV341/LMV342	20	32		
		Sourcing LMV344	18	24		mA
		Sinking	15	24		
t _{on}	Turn-on Time from Shutdown	(LMV341)		5		μs
V _{SD}	Shutdown Pin Voltage Range	ON Mode (LMV341)		1.7 to 2.7	2.4 to 2.7	V
		Shutdown Mode (LMV341)		0 to 1	0 to 0.8	V

2.7V AC Electrical Characteristics (Note 10)

Unless otherwise specified, all limits guaranteed for $T_J = 25^{\circ}C$, $V^+ = 2.7V$, $V^- = 0V$, $V_{CM} = V^+/2$, $V_O = V^+/2$ and $R_L > 1M\Omega$. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
			(Note 7)	(Note 6)	(Note 7)	
SR	Slew Rate	$R_L = 10k\Omega$, (Note 9)		1.0		V/µs
GBW	Gain Bandwidth Product	$R_L = 100k\Omega$, $C_L = 200pF$		1.0		MHz
Φ_{m}	Phase Margin	$R_L = 100k\Omega$		72		deg
G _m	Gain Margin	$R_L = 100k\Omega$		20		dB
e _n	Input-Referred Voltage Noise	f = 1kHz		40		nV/ √Hz
i _n	Input-Referred Current Noise	f = 1kHz		0.001		pA/ √Hz
THD	Total Harmonic Distortion	$f = 1kHz, A_V = +1$		0.017		%
		$R_L = 600\Omega$, $V_{IN} = 1V_{PP}$				

5V DC Electrical Characteristics (Note 10)

Unless otherwise specified, all limits guaranteed for T_J = 25°C, V^+ = 5V, V^- = 0V, V_{CM} = V+/2, V_O = V+/2 and R $_L$ > 1M Ω . Boldface limits apply at the temperature extremes.

			Min	Тур	Max	
Symbol	Parameter	Conditions	(Note 7)	(Note 6)	(Note 7)	Units
V _{os}	Input Offset Voltage	LMV341		0.025	4	
					4.5	mV
		LMV342/LMV344		0.70	5	IIIV
					5.5	
TCV _{OS}	Input Offset Voltage Average Drift			1.9		μV/°C
I _B	Input Bias Current			0.02	200	pA
					375	
Ios	Input Offset Current			6.6		fA
Is	Supply Current	Per Amplifier		107	200	μΑ
					260	
		Shutdown Mode, V _{SD} = 0V		0.033	1	μΑ
		(LMV341)			1.5	
CMRR	Common Mode Rejection	$0V \le V_{CM} \le 4.0V$	56	86		dB
	Ratio	$0V \le V_{CM} \le 3.9V$	50			
PSRR	Power Supply Rejection Ratio	$2.7V \le V^+ \le 5V$	65	82		dB
			60			
V _{CM}	Input Common Mode Voltage	For CMRR ≥ 50dB	0	-0.2 to 4.2	4	V
				(Range)		

5V DC Electrical Characteristics (Note 10) (Continued)

Unless otherwise specified, all limits guaranteed for $T_J = 25^{\circ}C$, $V^+ = 5V$, $V^- = 0V$, $V_{CM} = V^+/2$, $V_O = V^+/2$ and $R_L > 1M\Omega$. **Boldface** limits apply at the temperature extremes.

			Min	Тур	Max	
Symbol	Parameter	Conditions	(Note 7)	(Note 6)	(Note 7)	Units
A _V	Large Signal Voltage Gain	$R_L = 10k\Omega$ to 2.5V	78	116		_
	(Note 8)		70			dB
		$R_L = 2k\Omega$ to 2.5V	72	107		uБ
			64			
Vo	Output Swing	$R_L = 2k\Omega$ to 2.5V		32	60	
					95	mV
			60	34		IIIV
			95			
		$R_L = 10k\Omega$ to 2.5V		7	30	
					40	mV
			30	7		IIIV
			40			
Io	Output Short Circuit Current	Sourcing	85	113		Λ
		Sinking	50	75		mA
t _{on}	Turn-on Time from Shutdown	(LMV341)		5		μs
V _{SD}	Shutdown Pin Voltage Range	ON Mode (LMV341)		3.1 to 5	4.5 to 5.0	V
		Shutdown Mode (LMV341)		0 to 1	0 to 0.8	V

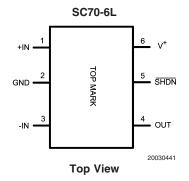
5V AC Electrical Characteristics (Note 10)

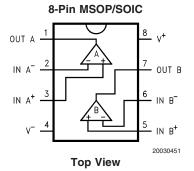
Unless otherwise specified, all limits guaranteed for $T_J = 25^{\circ}C$, $V^+ = 5V$, $V^- = 0V$, $V_{CM} = V^+/2$, $V_O = V^+/2$ and $R_L > 1M\Omega$. **Boldface** limits apply at the temperature extremes.

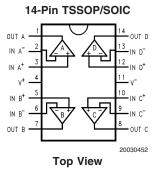
Symbol	Parameter	Conditions	Min	Тур	Max	Units
			(Note 7)	(Note 6)	(Note 7)	
SR	Slew Rate	$R_L = 10k\Omega$, (Note 9)		1.0		V/µs
GBW	Gain-Bandwidth Product	$R_L = 10k\Omega$, $C_L = 200pF$		1.0		MHz
Φ_{m}	Phase Margin	$R_L = 100k\Omega$		70		deg
G _m	Gain Margin	$R_L = 100k\Omega$		20		dB
e _n	Input-Referred Voltage Noise	f = 1kHz		39		nV/ √Hz
i _n	Input-Referred Current Noise	f = 1kHz		0.001		pA/ √Hz
THD	Total Harmonic Distortion	$f = 1 \text{ kHz}, A_V = +1$		0.012		%
		$R_L = 600\Omega$, $V_{IN} = 1V_{PP}$				

- Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not guaranteed. For guaranteed specifications and the test conditions, see the Electrical Characteristics.
- Note 2: Human body model, $1.5k\Omega$ in series with 100pF. Machine model, 0Ω in series with 200pF.
- Note 3: Shorting output to V^+ will adversely affect reliability.
- Note 4: Shorting output to V⁻ will adversely affect reliability.
- Note 5: The maximum power dissipation is a function of $T_{J(MAX)}$, θ_{JA} , and T_A . The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(MAX)} T_A)/\theta_{JA}$. All numbers apply for packages soldered directly into a PC board.
- Note 6: Typical values represent the most likely parametric norm.
- Note 7: All limits are guaranteed by testing or statistical analysis.
- Note 8: R_L is connected to mid-supply. The output voltage is GND + $0.2V \le V_O \le V^+$ -0.2V
- Note 9: Connected as voltage follower with 2V_{PP} step input. Number specified is the slower of the positive and negative slew rates.
- **Note 10:** Electrical Table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device such that $T_J = T_A$. No guarantee of parametric performance is indicated in the electrical tables under conditions of internal self heating where $T_J > T_A$.

Connection Diagrams





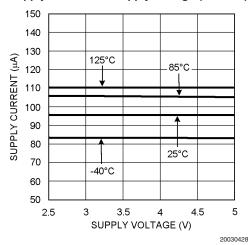


Ordering Information

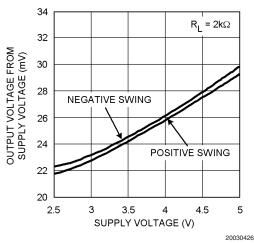
Package	Part Number	Package Marking	Transport Media	NSC Drawing	
	110/04/100		41117 T 18 1		
6-Pin SC70	LMV341MG	A78 1k Units Tape and Reel		MAA06A	
011110070	LMV341MGX	7470	3k Units Tape and Reel	IVIAAOOA	
8-Pin MSOP	LMV342MM	A82A	1k Units Tape and Reel	MUA08A	
0-FIII WISOF	LMV342MMX	AOZA	3.5k Units Tape and Reel		
8-Pin SOIC	LMV342MA	LMV342MA	95 Units/Rail	- M08A	
6-FIII 30IC	LMV342MAX	LIVI V 34ZIVIA	2.5k Units Tape and Reel	IVIOOA	
14-Pin TSSOP	LMV344MT	LMV344MT Rails 2.5k Units Tape and Reel		MTC14	
14-6111 13306	LMV344MTX				
14-Pin SOIC	LMV344MA	LMV344MA	55 Units/Rail	M14A	
14-1111 3010	LMV344MAX	LIVI V 344IVIA	2.5k Units Tape and Reel	IVI 14A	

Typical Performance Characteristics

Supply Current vs. Supply Voltage (LMV341)

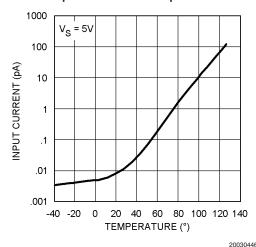


Output Voltage Swing vs. Supply Voltage

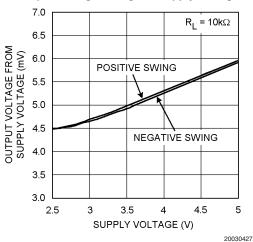


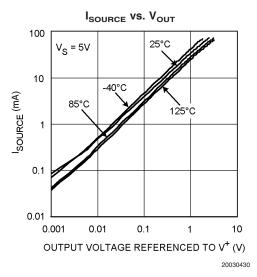
I_{SOURCE} vs. V_{OUT} 100 V_S = 2.7V 10 125°C SOURCE (mA) 85°C 0.1 25°C 0.01 0.001 0.01 0.001 0.1 10 OUTPUT VOLTAGE REFERENCED TO V+ (V) 20030429

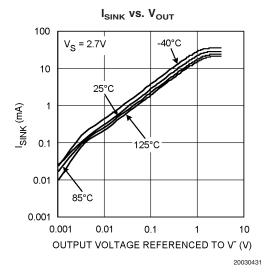
Input Current vs. Temperature

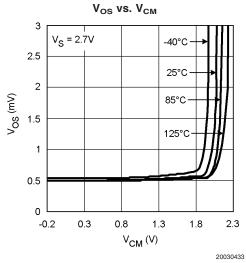


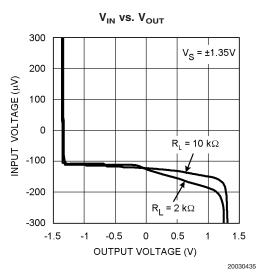
Output Voltage Swing vs. Supply Voltage

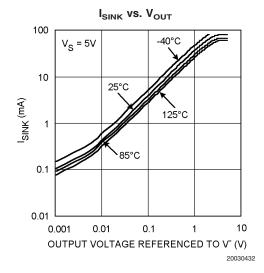


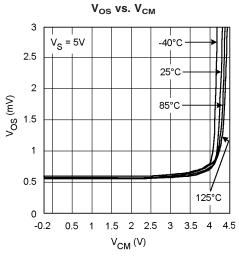


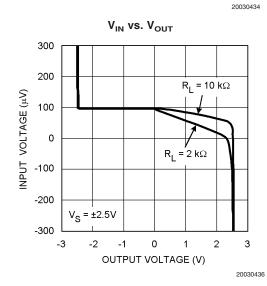




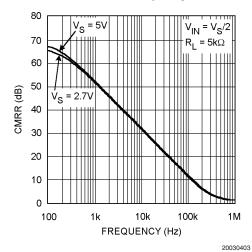




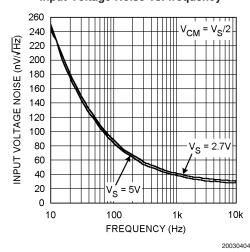




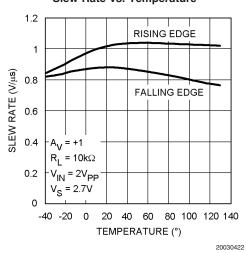
CMRR vs. Frequency



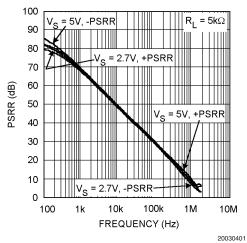
Input Voltage Noise vs. frequency



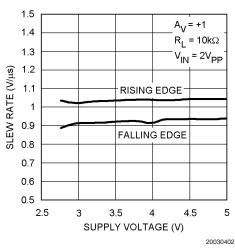
Slew Rate vs. Temperature



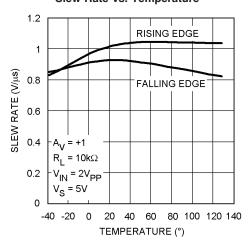
PSRR vs. Frequency



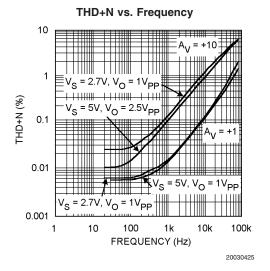
Slew Rate vs. V_{SUPPLY}



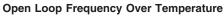
Slew Rate vs. Temperature

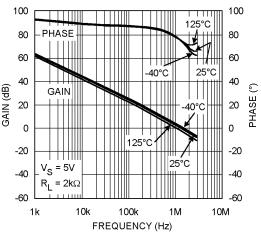


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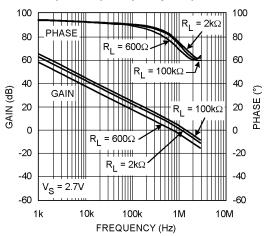


THD+N vs. V_{OUT} 10 $V_S = 2.7V, A_V = +10$ $V_S = 5V, A_V = +10$ 0.01 0.001 0.001 0.01 1 1 0.001 0.01 0.01 0.01 0.01 0.01 0.01 0.001 0.01 0.01 0.01 0.01 0.001



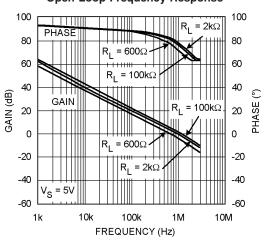


Open Loop Frequency Response

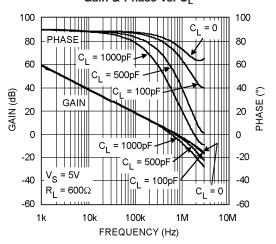


Open Loop Frequency Response

20030421

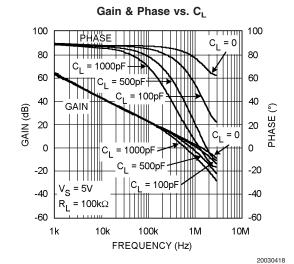


Gain & Phase vs. C_L

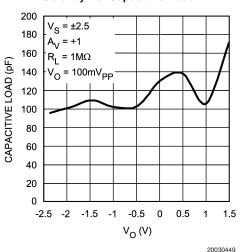


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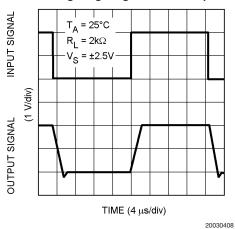
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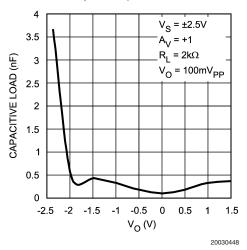
Stability vs. Capacitive Load



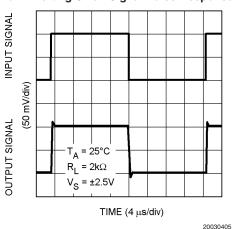
Non-Inverting Large Signal Pulse Response



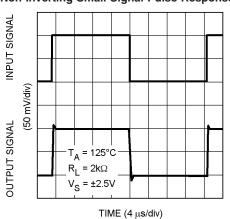
Stability vs. Capacitive Load



Non-Inverting Small Signal Pulse Response

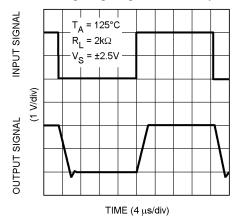


Non-Inverting Small Signal Pulse Response



20030406

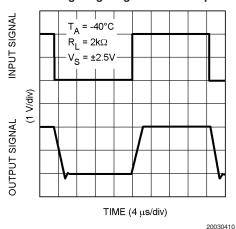
Non-Inverting Large Signal Pulse Response



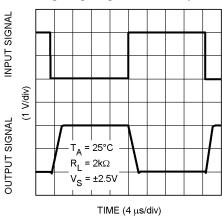
Non-Inverting Large Signal Pulse Response

20030409

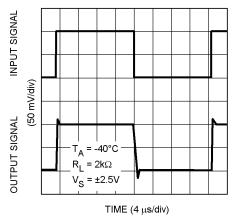
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Inverting Large Signal Pulse Response

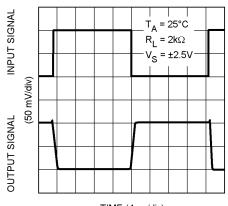


Non-Inverting Small Signal Pulse Response



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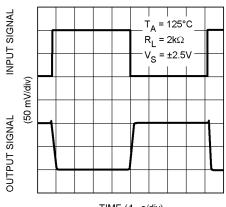
Inverting Small Signal Pulse Response



TIME (4 µs/div)

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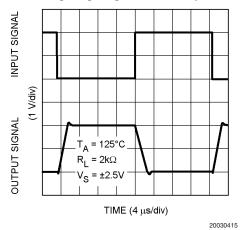
Inverting Small Signal Pulse Response



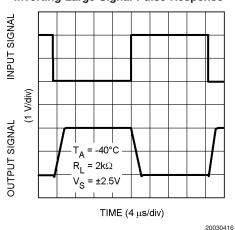
TIME (4 µs/div)

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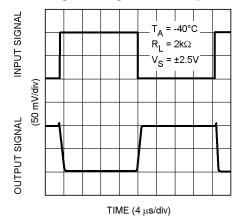
Inverting Large Signal Pulse Response



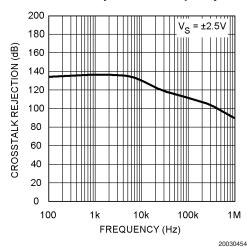
Inverting Large Signal Pulse Response



Inverting Small Signal Pulse Response



Crosstalk Rejection vs. Frequency



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Application Section

LMV341/342/344

The LMV341/342/344 family of amplifiers features low voltage, low power, and rail-to-rail output operational amplifiers designed for low voltage portable applications. The family is designed using all CMOS technology. This results in an ultra low input bias current. The LMV341 has a shutdown option, which can be used in portable devices to increase battery life

A simplified schematic of the LMV341/342/344 family of amplifiers is shown in *Figure 1*. The PMOS input differential pair allows the input to include ground. The output of this differential pair is connected to the Class AB turnaround stage. This Class AB turnaround has a lower quiescent current, compared to regular turnaround stages. This results in lower offset, noise, and power dissipation, while slew rate equals that of a conventional turnaround stage. The output of the Class AB turnaround stage provides gate voltage to the complementary common-source transistors at the output stage. These transistors enable the device to have rail-to-rail output.

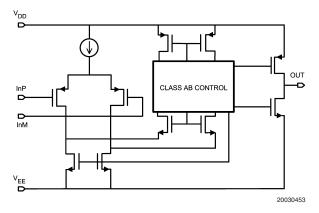


FIGURE 1. Simplified Schematic

CLASS AB TURNAROUND STAGE AMPLIFIER

This patented folded cascode stage has a combined class AB amplifier stage, which replaces the conventional folded cascode stage. Therefore, the class AB folded cascode stage runs at a much lower quiescent current compared to conventional folded cascode stages. This results in significantly smaller offset and noise contributions. The reduced offset and noise contributions in turn reduce the offset voltage level and the voltage noise level at the input of the LMV341/342/344. Also the lower quiescent current results in a high open-loop gain for the amplifier. The lower quiescent current does not affect the slew rate of the amplifier nor its ability to handle the total current swing coming from the input stage.

The input voltage noise of the device at low frequencies, below 1kHz, is slightly higher than devices with a BJT input stage; However the PMOS input stage results in a much lower input bias current and the input voltage noise drops at frequencies above 1kHz.

SAMPLE AND HOLD CIRCUIT

The lower input bias current of the LMV341 results in a very high input impedance. The output impedance when the device is in shutdown mode is quite high. These high imped-

ances, along with the ability of the shutdown pin to be derived from a separate power source, make LMV341 a good choice for sample and hold circuits. The sample clock should be connected to the shutdown pin of the amplifier to rapidly turn the device on or off.

Figure 2 shows the schematic of a simple sample and hold circuit. When the sample clock is high the first amplifier is in normal operation mode and the second amplifier acts as a buffer. The capacitor, which appears as a load on the first amplifier, will be charging at this time. The voltage across the capacitor is that of the non-inverting input of the first amplifier since it is connected as a voltage-follower. When the sample clock is low the first amplifier is shut off, bringing the output impedance to a high value. The high impedance of this output, along with the very high impedance on the input of the second amplifier, prevents the capacitor from discharging. There is very little voltage droop while the first amplifier is in shutdown mode. The second amplifier, which is still in normal operation mode and is connected as a voltage follower, also provides the voltage sampled on the capacitor at its output.

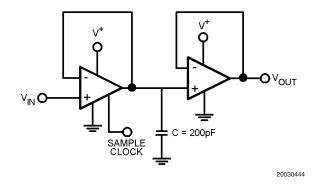


FIGURE 2. Sample and Hold Circuit

SHUTDOWN FEATURE

The LMV341 is capable of being turned off in order to conserve power and increase battery life in portable devices. Once in shutdown mode the supply current is drastically reduced, $1\mu A$ maximum, and the output will be "tri-stated."

The device will be disabled when the shutdown pin voltage is pulled low. The shutdown pin should never be left unconnected. Leaving the pin floating will result in an undefined operation mode and the device may oscillate between shutdown and active modes.

The LMV341 typically turns on 2.8µs after the shutdown voltage is pulled high. The device turns off in less than 400ns after shutdown voltage is pulled low. Figure 3 and Figure 4 show the turn-on and turn-off time of the LMV341, respectively. In order to reduce the effect of the capacitance added to the circuit by the scope probe, in the turn-off time circuit a resistive load of 600Ω is added. Figure 5 and Figure 6 show the test circuits used to obtain the two plots.

Application Section (Continued)

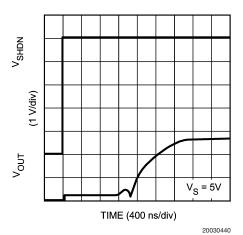


FIGURE 3. Turn-on Time

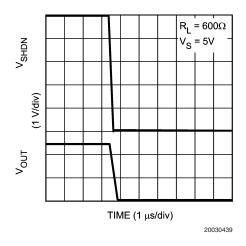


FIGURE 4. Turn-off Time

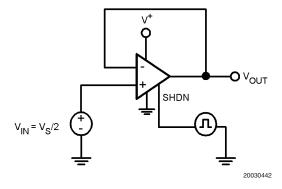


FIGURE 5. Turn-on Time

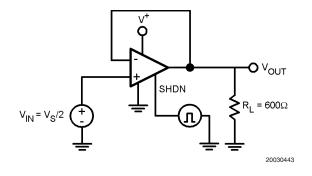


FIGURE 6. Turn-off Time

LOW INPUT BIAS CURRENT

The LMV341/LMV342/LMV344 Amplifiers have a PMOS input stage. As a result, they will have a much lower input bias current than devices with BJT input stages. This feature makes these devices ideal for sensor circuits. A typical curve of the input bias current of the LMV341 is shown in *Figure 7*.

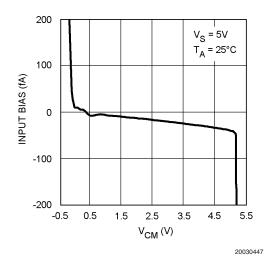
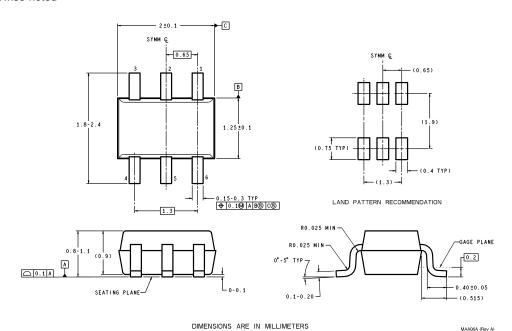


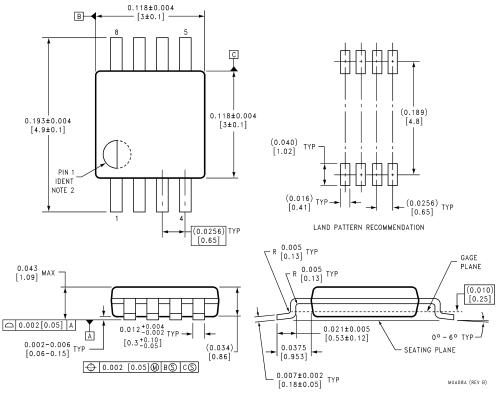
FIGURE 7. Input Bias Current vs. $V_{\rm CM}$

Physical Dimensions inches (millimeters) unless otherwise noted



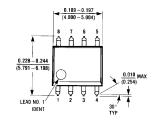
6-Pin SC70

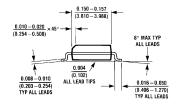
NS Package Number MAA06A

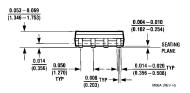


8-Pin MSOP **NS Package Number MUA08A**

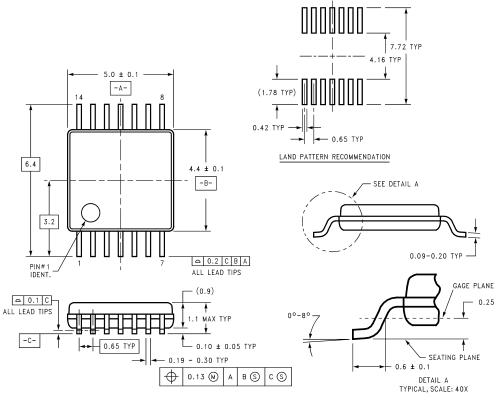
Physical Dimensions inches (millimeters) unless otherwise noted (Continued)







8-Pin SOIC NS Package Number M08A

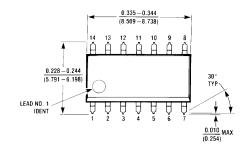


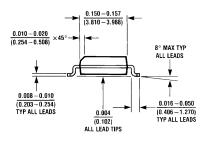
DIMENSIONS ARE IN MILLIMETERS

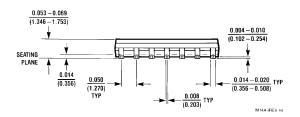
MTC14 (REV C)

14-Pin TSSOP NS Package Number MTC14

Physical Dimensions inches (millimeters) unless otherwise noted (Continued)







14-Pin SOIC **NS Package Number M14A**

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